

Fast Facts

Power Module for Inverters Half bridge or B6 bridge configuration

GaN Power Module - Gallium nitride semiconductor half-bridge module: 650 V – up to 500 A
SiC Power Module - Silicon carbide semiconductor half-bridge module: 750 V / 1200 V – up to 500 A

Technology

- 175 °C operating temperature
- Ultra small footprint
- Scalable circuit design
- Ultra low loss
- Silicon nitride ceramic substrate
- ECPE AQG 324 qualified

Key Technologies

- TLPS and lead frame attachment
- Low inductive lead frame and package design
- Transfer molding

